

SOT-323 BIPOLAR TRANSISTORS
TRANSISTOR (PNP)

FEATURES

- * Power dissipation
Pcm: 0.2 W (Tamb=25°C)
- * Collector current
Icm: -0.2 A
- * Collector-base voltage
V(BR)CBO: -40 V
- * Operating and storage junction temperature range
Tj,Tstg: -55°C to +150°C

MECHANICAL DATA

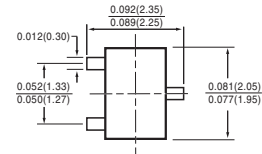
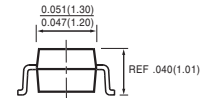
- * Case: Molded plastic
- * Epoxy: UL 94V-O rate flame retardant
- * Lead: MIL-STD-202E method 208C guaranteed
- * Mounting position: Any
- * Weight: 0.006 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.



SOT-323



Dimensions in inches and (millimeters)

MAXIMUM RATINGS (@ TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	VALUE	UNITS
Zener Current (see Table "Characteristics")	-	-	-
Max. Steady State Power Dissipation (1)	P _D	200	mW
Max. Operating Temperature Range	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (@ TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Thermal Resistance Junction to Ambient (1)	R θ _{JA}	-	-	625	°C/W
Max. Instantaneous Forward Voltage at I _F = 10mA	V _F	-	-	-	Volts

NOTES : 1.Valid provided that terminals are kept at ambient temperature.

ELECTRICAL CHARACTERISTICS (@TA=25°C unless otherwise noted)

Chatacteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS (2)

Collector-Emitter Breakdown Voltage ($I_C = -1.0\text{mA}$, $I_B = 0$)	$V_{(BR)CEO}$	-40	-	Vdc
Collector-Base Breakdown Voltage ($I_C = -10\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	-40	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ($V_{CE} = -40\text{Vdc}$, $I_B = 0$)	I_{CEO}	-	-0.1	μA
Collector Cutoff Current ($V_{CB} = -40\text{Vdc}$, $I_E = 0$)	I_{CBO}	-	-0.1	μA
Emitter Cutoff Current ($V_{EB} = -5\text{Vdc}$, $I_C = 0$)	I_{EBO}	-	-0.1	μA
Base Cutoff Current ($V_{CE} = -30\text{Vdc}$, $V_{EB(off)} = -3.0\text{Vdc}$)	I_{BL}	-	-50	nA

ON CHARACTERISTICS (2)

DC Current Gain ($I_C = -100\mu\text{A}$, $V_{CE} = -1.0\text{Vdc}$)	hFE	60	-	-
($I_C = -1.0\text{mA}$, $V_{CE} = -1.0\text{Vdc}$)		80	-	
($I_C = -10\text{mA}$, $V_{CE} = -1.0\text{Vdc}$)		100	300	
($I_C = -50\text{mA}$, $V_{CE} = -1.0\text{Vdc}$)		60	-	
($I_C = -100\text{mA}$, $V_{CE} = -1.0\text{Vdc}$)		30	-	
Collector-Emitter Saturation Voltage ($I_C = -10\text{mA}$, $I_B = -1.0\text{mA}$)	$V_{CE(sat)}$	-	-0.20	Vdc
($I_C = -50\text{mA}$, $I_B = -5.0\text{mA}$)		-	-0.30	
Base-Emitter Saturation Voltage ($I_C = -10\text{mA}$, $I_B = -1.0\text{mA}$)	$V_{BE(sat)}$	-0.65	-0.85	Vdc
($I_C = -50\text{mA}$, $I_B = -5.0\text{mA}$)		-	-0.95	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product ($I_C = -10\text{mA}$, $V_{CE} = -20\text{Vdc}$, $f = 1.0\text{kHz}$)	f_T	300	-	MHz
Output Capacitance ($V_{CB} = -5.0\text{Vdc}$, $I_E = 0$, $f = 1.0\text{MHz}$)	C_{obo}	-	4.5	pF
Input Capacitance ($V_{EB} = -0.5\text{Vdc}$, $I_C = 0$, $f = 1.0\text{MHz}$)	C_{ibo}	-	10	pF
Input Impedance ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{ie}	2.0	12	k Ω
Voltage Feedback Ratio ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{re}	0.1	10	$\times 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{fe}	100	400	-
Output Admittance ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{oe}	3.0	60	μs
Noise Figure ($I_C = -100\mu\text{A}$, $V_{CE} = -5.0\text{Vdc}$, $R_S = 1.0\text{k}\Omega$, $f = 1.0\text{kHz}$)	NF	-	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = -3\text{Vdc}$, $V_{BE} = -0.5\text{Vdc}$, $I_C = -10\text{mA}$, $I_{B1} = -1\text{mA}$)	t_d	-	35	ns
Rise Time		t_r	-	35	
Storage Time	$(V_{CC} = -3\text{Vdc}$, $I_C = -10\text{mA}$, $I_{B1} = I_{B2} = -1\text{mA}$)	t_s	-	225	ns
Fall Time		t_f	-	75	

NOTES : 2. Pulse Test: Pulse Width \leq 300 μs , Duty Cycle \leq 2.0%